MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK35N65W

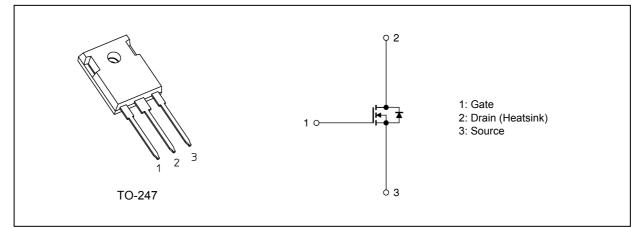
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.068 \Omega$ (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: V_{th} = 2.5 to 3.5 V ($V_{\rm DS}$ = 10 V, $I_{\rm D}$ = 2.1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics			Rating	Unit
Drain-source voltage		V _{DSS}	650	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	Ι _D	35	A
Drain current (pulsed)	(Note 1)	I _{DP}	140	
Power dissipation $(T_c = 25^{\circ}C)$		PD	270	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	614	mJ
Avalanche current		I _{AR}	8.8	A
Reverse drain current (DC)	(Note 1)	I _{DR}	35	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	140	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	
Mounting torque		TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.463	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	50	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 14 mH, R_G = 25 Ω , I_{AR} = 8.8 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

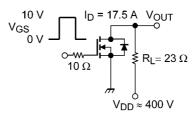
6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	650	_	—	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 2.1 mA	2.5	—	3.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 17.5 A		0.068	0.08	Ω

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz	_	4100	_	pF
Reverse transfer capacitance	C _{rss}]		9	—	
Output capacitance	C _{oss}]		90	_	
Effective output capacitance	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V	_	130	—	
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	2	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1	_	30	—	ns
Switching time (turn-on time)	t _{on}]		70	—	
Switching time (fall time)	t _f]		8	_	
Switching time (turn-off time)	t _{off}	1		150	_	
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 17.5 A	50	_	_	V/ns



 $Duty \leq 1\%, \ t_w = 10 \ \mu s$ Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} \text{ = } 10 \text{V}, \text{I}_{D} \text{ = } 35 \text{ A}$	—	100	—	nC
Gate-source charge 1	Q _{gs1}			25	_	
Gate-drain charge	Q _{gd}		_	35	_	

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 35 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 17.5 A, V _{GS} = 0 V	_	430	_	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 50 A/μs	_	4.2	_	μC
Peak reverse recovery current	I _{rr}		_	21	_	Α
Diode dv/dt ruggedness	dv/dt	I _{DR} = 17.5 A, V _{GS} = 0 V, V _{DD} = 400 V	15	_	_	V/ns

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TOSHIBA 7. Marking (Note)

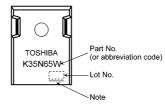


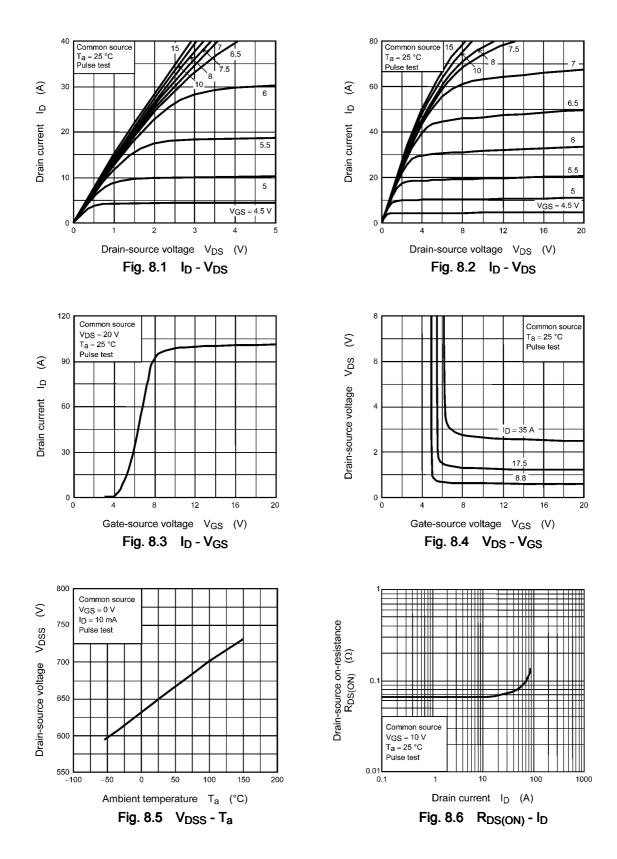
Fig. 7.1 Marking

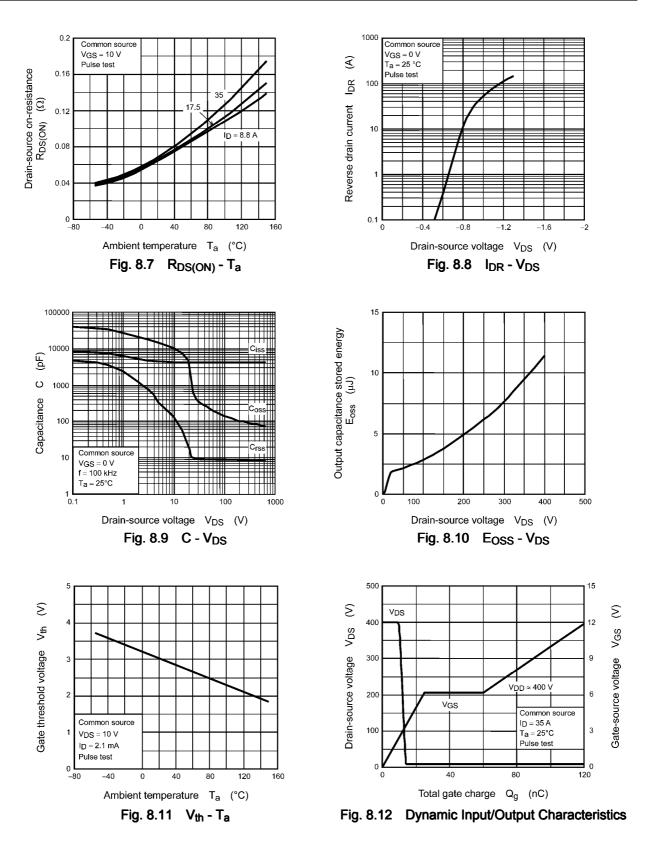
 Note:
 A line under a Lot No. identifies the indication of product Labels.

 Not underlined: [[Pb]]/INCLUDES > MCV
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8. Characteristics Curves (Note)





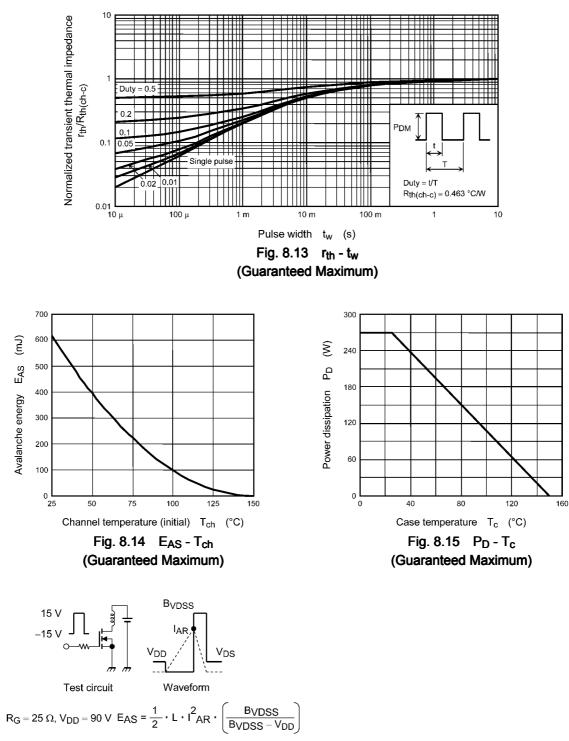
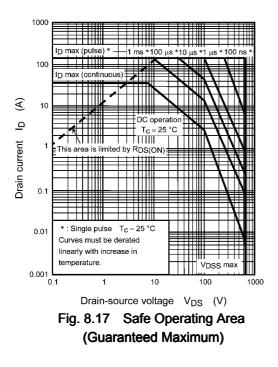


Fig. 8.16 Test Circuit/Waveform

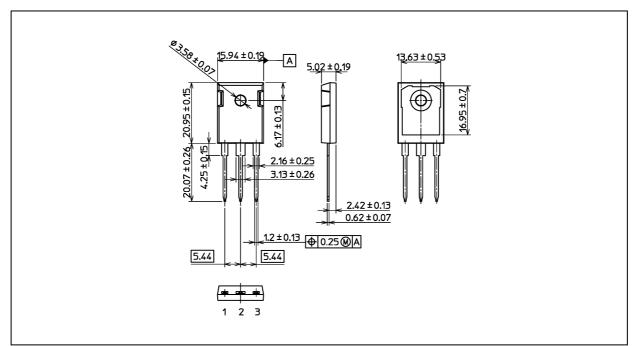


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

F	Package Name(s)
JEITA: SC-65	
TOSHIBA: 2-16L1A	
Nickname: TO-247	

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